

ABSTRACT

**Method For Manufacturing A Monocrystalline Layer Of GaAs Material
And Substrate For Epitaxial Growth Of A Monocrystalline Layer Of
5 GaAs Material**

A process for producing a monocrystalline layer of GaAs material comprising
the transfer of a monocrystalline seed layer of SrTiO_3 material to a carrier
substrate of silicon material followed by epitaxial growth of a monocrystalline
10 layer of GaAs material.

Figure 2